SZCJ

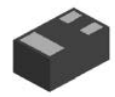
Shenzhen Changji Semiconductor Co., LTD.

DFN1006-3L-A Plastic-Encapsulate MOSFETs

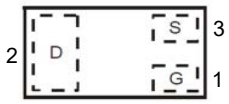
CJBB3139K P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
-20V	520mΩ@-4.5V	-0.66A
	780mΩ@-2.5V	
	950mΩ(TYP)@-1.8V	

DFN1006-3L-A



Bottom View



Top View
Internal Schematic

FEATURE

- Lead Free Product is Acquired
- Surface Mount Package
- P-Channel Switch with Low R_{DS}(on)
- Operated at Low Logic Level Gate Drive
- ESD Protected Gate

APPLICATION

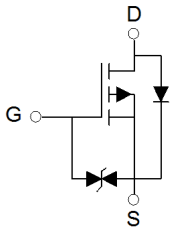
- Load/ Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING:



Top View

Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Typical Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (note 1)	I_D	-0.66	A
Pulsed Drain Current (tp=10us)	I_{DM}	-2.64	A
Power Dissipation (note 1)	P_D	275	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	455	℃/W
Operation Junction and Storage Temperature Range	T_J,T_{STG}	-55~ 150	℃
Lead Temperature for Soldering Purposes(1/8'' from case for 10 s)	T_L	260	℃

MOSFET ELECTRICAL CHARACTERISTICS

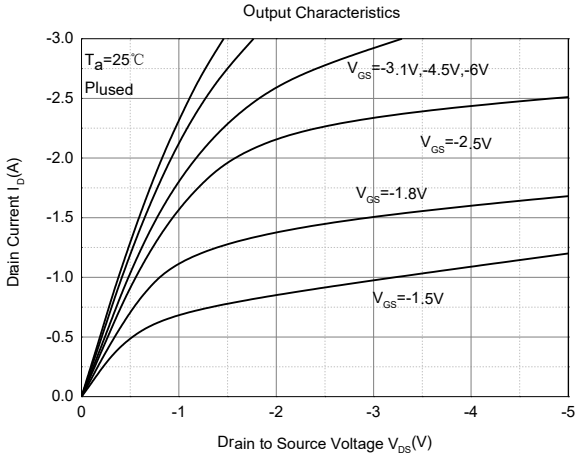
T_a=25℃ unless otherwise noted

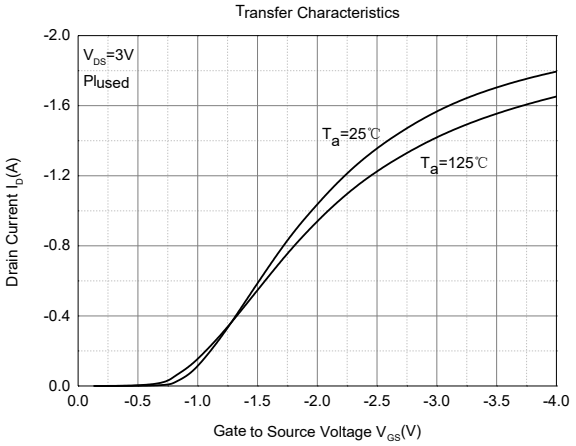
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-20V,V_{GS} = 0V			-1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±10V, V_{DS} = 0V			±20	uA
Gate threshold voltage (note 2)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.35	-0.61	-1.1	V
Drain-source on-resistance(note 2)	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-1A		450	520	mΩ
		V_{GS} =-2.5V, I_D =-0.8A		650	780	mΩ
		V_{GS} =-1.8V, I_D =-0.5A		950		mΩ
Forward tranconductance(note 2)	g_{FS}	V_{DS} =-10V, I_D =-0.54A		1.2		S
Diode forward voltage	V_{SD}	I_S=-0.5A, V_{GS} = 0V			-1.2	V
DYNAMIC PARAMETERS(note 4)						
Input Capacitance	C_{iss}	V_{DS} =-16V,V_{GS} =0V,f =1MHz		113		pF
Output Capacitance	C_{oss}			15		pF
Reverse Transfer Capacitance	C_{rss}			9		pF
SWITCHING PARAMETERS (note 4)						
Turn-on delay time (note 3)	$t_{d(on)}$	V_{DD}=-4.5V,V_{GS}=-10V, I_D=-200mA,R_{GEN}=10Ω		9		ns
Turn-on rise time (note 3)	t_r			5.7		ns
Turn-off delay time (note 3)	$t_{d(off)}$			32.6		ns
Turn-off fall time (note 3)	t_f			20.3		ns

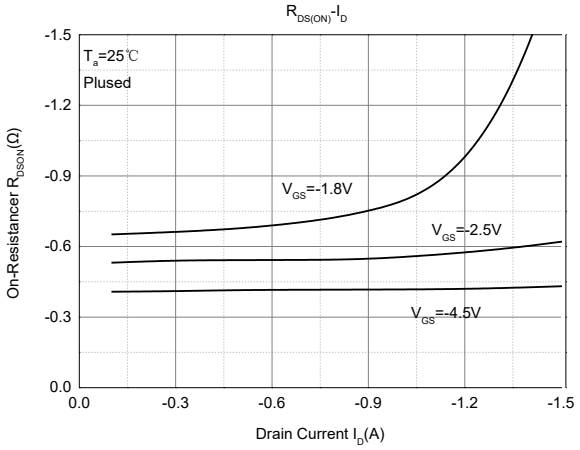
Notes:

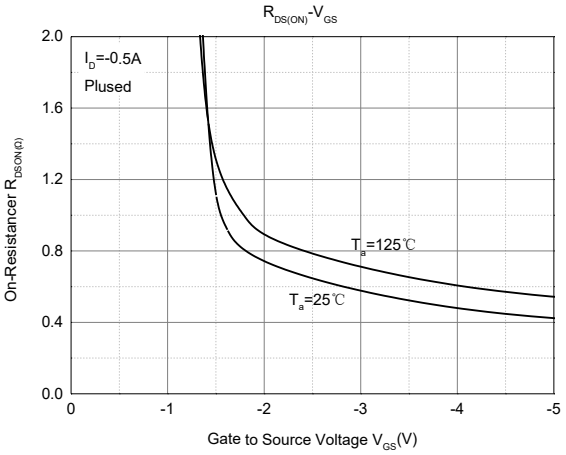
1. Surface mounted on FR4 board using 1 square inch pad size, 1oz copper.
2. Pulse Test : Pulse Width=300μs, Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producting.

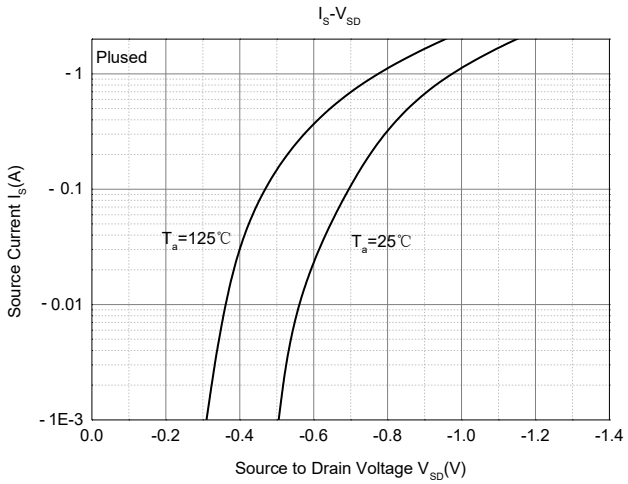
Typical Characteristics

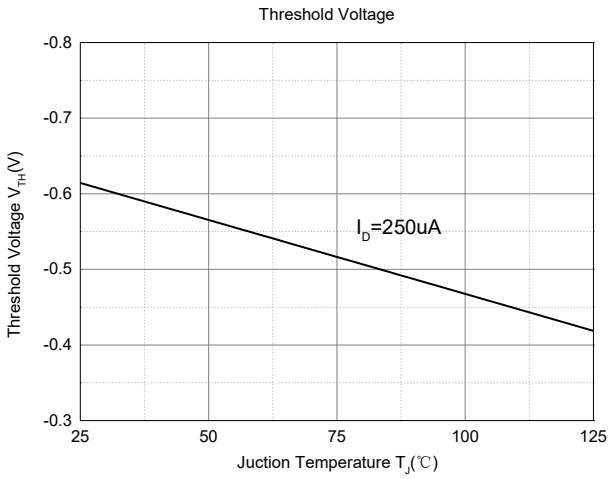




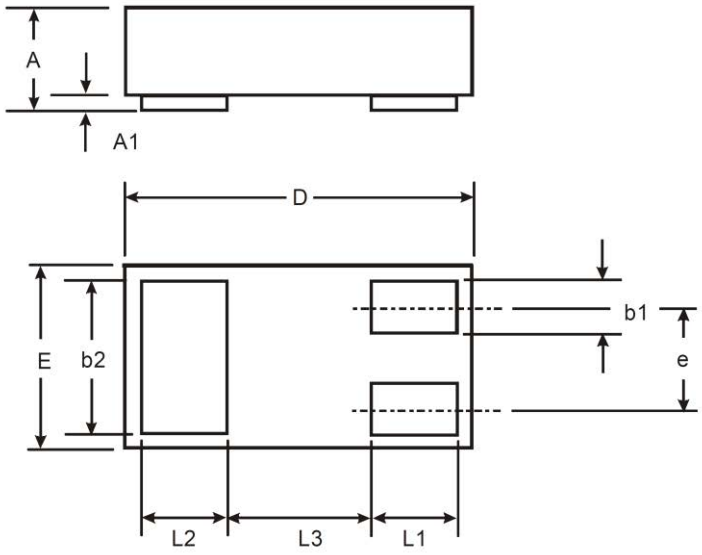






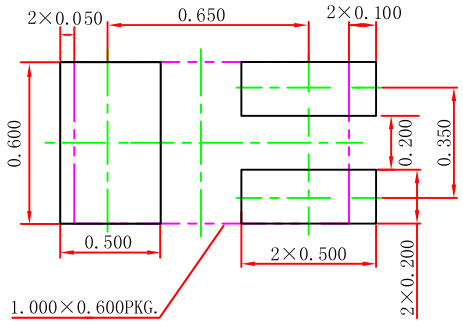


DFN1006-3L-A Package Outline Dimensions



DFN1006-3L-A			
Dim	**Min.**	**Max.**	**Typ.**
A	0.34	0.40	0.37
A1	0.00	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
All Dimensions in mm			

DFN1006-3L-A Suggested Pad Layout



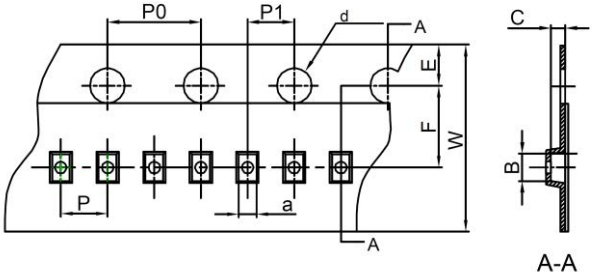
Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.050mm.
3.The pad layout is for reference purposes only.

NOTICE

SZCJ reserves the right to make modifications,enhan nts,improvements,corrections or other es without further notice to any product herein. SZCJ does not assume any liability arising out of the application or use of any product described h

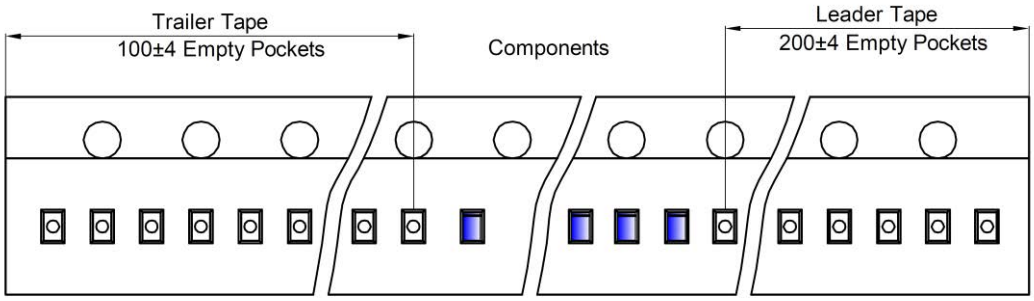
DFN1006-3L-A Tape and Reel

DFN1006-3L-A Embossed Carrier Tape

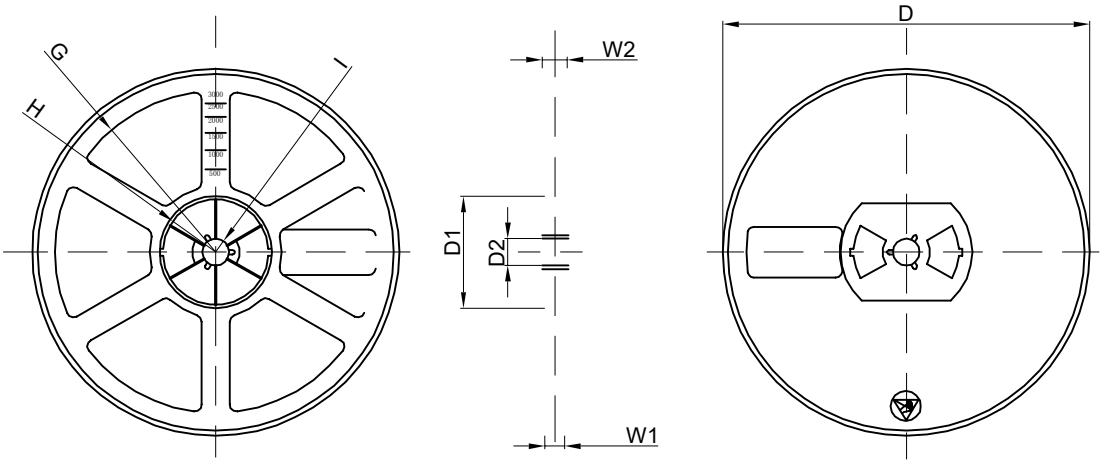


Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFN1006-3L-A	0.66	1.15	0.66	Ø1.50	1.75	3.50	4.00	2.00	2.00	8.00

DFN1006-3L-A Tape Leader and Trailer



DFN1006-3L-A Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
10000 pcs	7 inch	150,000 pcs	203×203×195	600,000 pcs	438×438×220	